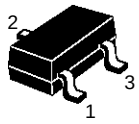
SGS-THOMSON MICROELECTRONICS

BFS20

SMALL SIGNAL NPN TRANSISTOR

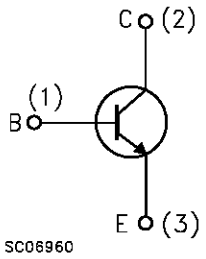
Type	Marking
BFS20	G1

- SILICON EPITAXIAL PLANAR NPN TRANSISTORS
- MINIATURE PLASTIC PACKAGE FOR APPLICATION IN SURFACE MOUNTING CIRCUITS
- COMMON EMITTER IF AMPLIFIER



SOT-23

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage (I_E = 0)	30	V
V_{CEO}	Collector-Emitter Voltage (I_B = 0)	20	V
V_{EBO}	Emitter-Base Voltage (I_C = 0)	4	V
I_C	Collector Current	25	mA
I_{CM}	Collector Peak Current	25	mA
I_B	Base Current	2	mA
P_{tot}	Total Dissipation at T_c = 25 °C	200	mW
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

THERMAL DATA

$R_{thj\text{-}amb}$ •	Thermal Resistance Junction-Ambient	Max	350	°C/W
$R_{thj\text{-}SR}$ •	Thermal Resistance Junction-Substrate	Max	290	°C/W

• Mounted on a ceramic substrate area = 15 x 15 x 0.6 mm

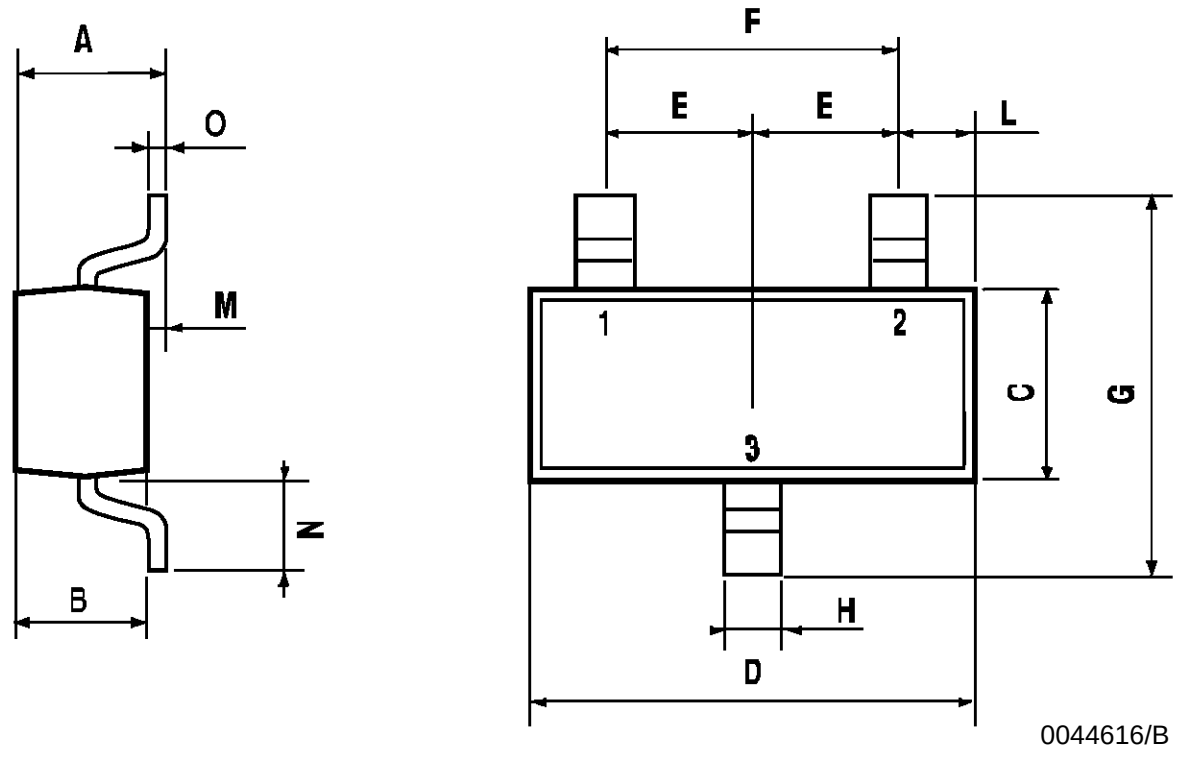
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current (I_E = 0)	V_{CB} = 20 V V_{CB} = 20 V T_j = 100 °C			100 10	nA µA
$V_{(BR)CBO}$*	Collector-Base Breakdown Voltage (I_E = 0)	I_C = 10 µA	30			V
$V_{(BR)CEO}$*	Collector-Emitter Breakdown Voltage (I_B = 0)	I_C = 2 mA	20			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage (I_C = 0)	I_E = 10 µA	4			V
$V_{BE(on)}$*	Base-Emitter On Voltage	I_C = 7 mA V_{CE} = 10 V		0.75	0.9	V
h_{FE}*	DC Current Gain	I_C = 7 mA V_{CE} = 10 V	40			
f_T	Transition Frequency	I_C = 7 mA V_{CE} = 10 V f = 100 MHz	275	550		MHz
C_{CB}	Collector Base Capacitance	I_E = 0 mA V_{CB} = 10 V f = 1MHz (emitter grounded)		0.35		pF
C_{CB}	Collector Base Capacitance	I_E = 0 mA V_{CB} = 10 V f = 1MHz (emitter open)		0.8		pF

* Pulsed: Pulse duration = 300 µs, duty cycle ≤ 2 %

SOT-23 MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.85		1.1	33.4		43.3
B	0.65		0.95	25.6		37.4
C	1.20		1.4	47.2		55.1
D	2.80		3	110.2		118
E	0.95		1.05	37.4		41.3
F	1.9		2.05	74.8		80.7
G	2.1		2.5	82.6		98.4
H	0.38		0.48	14.9		18.8
L	0.3		0.6	11.8		23.6
M	0		0.1	0		3.9
N	0.3		0.65	11.8		25.6
O	0.09		0.17	3.5		6.7



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